

BLF8G38LS-75V

Power LDMOS transistor

Rev. 1 — 4 November 2013

Objective data sheet

1. Product profile

1.1 General description

75 W LDMOS power transistor with improved video bandwidth for base station applications at frequencies from 3400 MHz to 3800 MHz.

Table 1. Typical performance

Typical RF performance at $T_{case} = 25\text{ °C}$ in a common source class-AB production test circuit.

Test signal	f (MHz)	I_{Dq} (mA)	V_{DS} (V)	$P_{L(AV)}$ (W)	G_p (dB)	η_D (%)	ACPR _{5M} (dBc)
1-carrier W-CDMA	3400 to 3800	600	30	20	15.5	26	-30 [1]

[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth
- Designed for broadband operation (3400 MHz to 3800 MHz)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

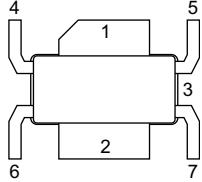
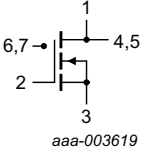
1.3 Applications

- RF power amplifiers for base stations and multi carrier applications in the 3400 MHz to 3800 MHz frequency range



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain		 aaa-003619
2	gate		
3	source [1]		
4	decoupling lead		
5	decoupling lead		
6	n.c.		
7	n.c.		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF8G38LS-75V	-	earless flanged LDMOST ceramic package; 6 leads	SOT1239B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		[1] -	225	°C

[1] Continuous use at maximum temperature will affect the reliability.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C}$; $P_L = 20\text{ W}$	0.48	K/W

6. Characteristics

Table 6. DC characteristics

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 1\text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}; I_D = 153\text{ mA}$	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 30\text{ V}; I_D = 600\text{ mA}$	1.7	2.0	2.5	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}; V_{DS} = 28\text{ V}$	-	-	2.8	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V};$ $V_{DS} = 10\text{ V}$	-	19.7	-	A
I_{GSS}	gate leakage current	$V_{GS} = 11\text{ V}; V_{DS} = 0\text{ V}$	-	-	280	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}; I_D = 153\text{ mA}$	-	0.9	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V};$ $I_D = 5.35\text{ A}$	-	0.1	-	Ω

Table 7. RF characteristics

Test signal: 1-carrier W-CDMA, 3GPP test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on the CCDF; $f_1 = 3400\text{ MHz}; f_2 = 3500\text{ MHz}; f_3 = 3600\text{ MHz}$; RF performance at $V_{DS} = 30\text{ V}; I_{Dq} = 600\text{ mA}; T_{case} = 25\text{ }^\circ\text{C}$; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_p	power gain	$P_{L(AV)} = 20\text{ W}$	14.3	15.5	-	dB
η_D	drain efficiency	$P_{L(AV)} = 20\text{ W}$	21	26	-	%
RL_{in}	input return loss	$P_{L(AV)} = 20\text{ W}$	-	-10	-6	dB
$ACPR_{5M}$	adjacent channel power ratio (5 MHz)	$P_{L(AV)} = 20\text{ W}$	-	-30	-25	dBc

7. Test information

7.1 Ruggedness in class-AB operation

The BLF8G38LS-75V is capable of withstanding a load mismatch corresponding to $VSWR = 10 : 1$ through all phases under the following conditions: $V_{DS} = 30\text{ V}; I_{Dq} = 600\text{ mA}; P_L = 75\text{ W}; f = 3400\text{ MHz}$.

7.2 Test circuit

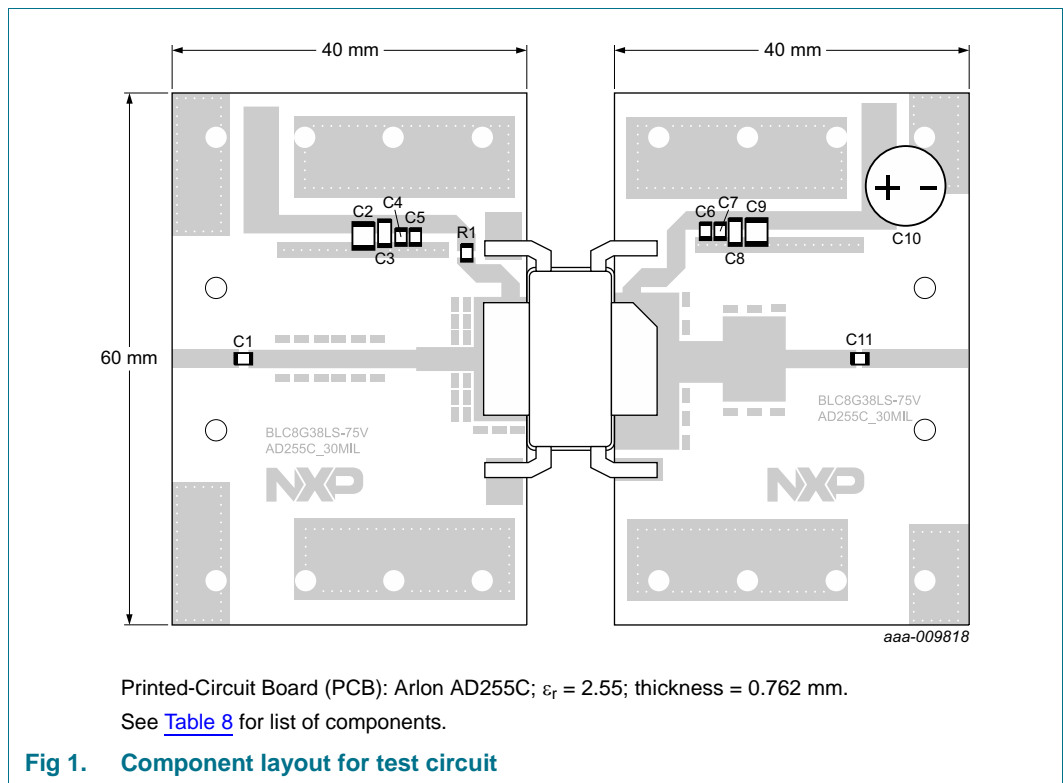


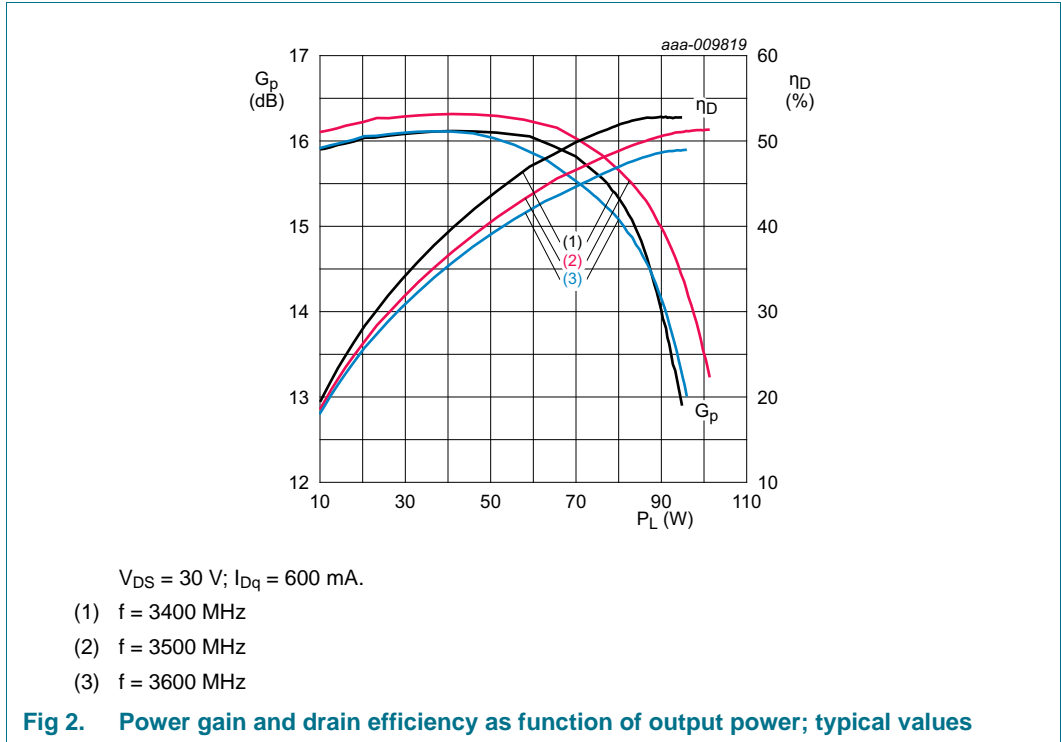
Table 8. List of components

For test circuit, see [Figure 1](#).

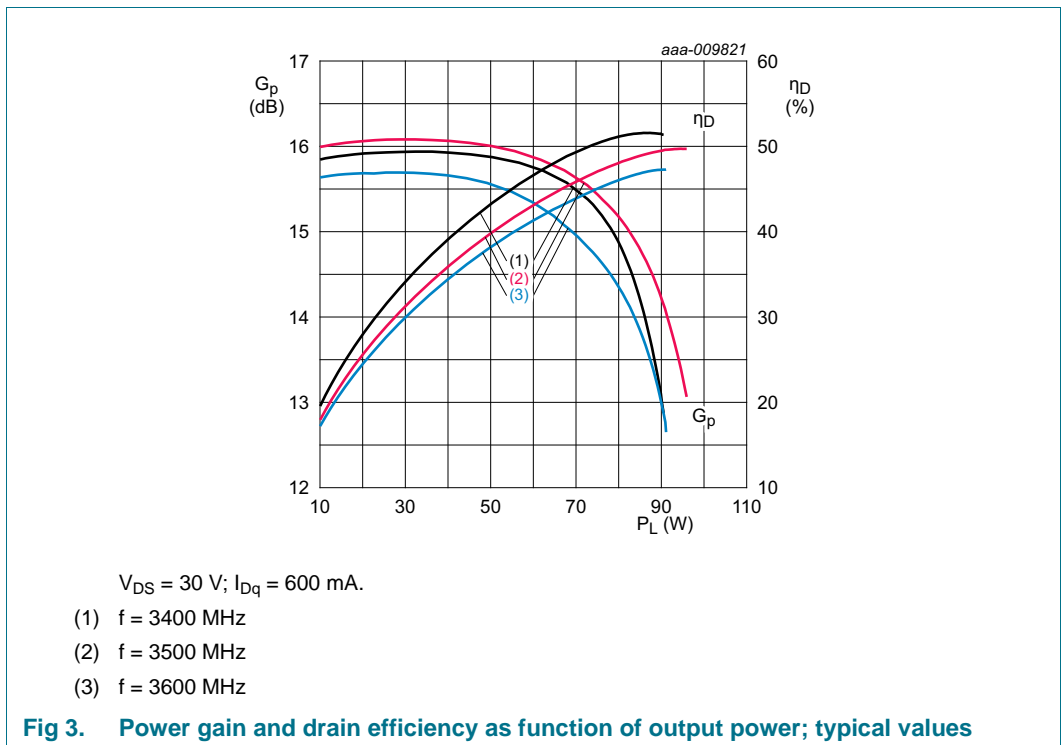
Component	Description	Value	Remarks
C1, C5, C6, C11	multilayer ceramic chip capacitor	20 pF	ATC600F
C2, C9	multilayer ceramic chip capacitor	10 μ F	Murata
C3, C8	multilayer ceramic chip capacitor	0.1 μ F	Murata
C4, C7	multilayer ceramic chip capacitor	0.01 μ F	Murata
C10	electrolytic capacitor	1000 μ F, 100 V	
R1	chip resistor	5.1 Ω	Vishay Dale SMD 0805

7.3 Graphical data

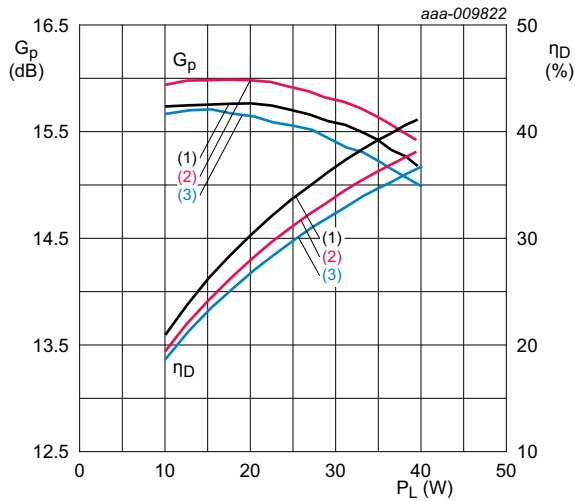
7.3.1 Pulsed CW



7.3.2 CW

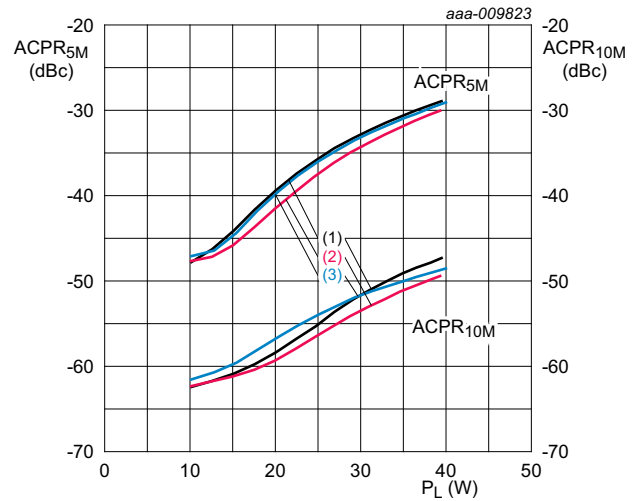


7.3.3 1-Carrier W-CDMA



$V_{DS} = 30\text{ V}; I_{Dq} = 600\text{ mA}.$
 (1) $f = 3400\text{ MHz}$
 (2) $f = 3500\text{ MHz}$
 (3) $f = 3600\text{ MHz}$

Fig 4. Power gain and drain efficiency as function of output power; typical values



$V_{DS} = 30\text{ V}; I_{Dq} = 600\text{ mA}.$
 (1) $f = 3400\text{ MHz}$
 (2) $f = 3500\text{ MHz}$
 (3) $f = 3600\text{ MHz}$

Fig 5. Adjacent channel power ratio (5 MHz) and adjacent channel power ratio (10 MHz) as function of output power; typical values

8. Package outline

Earless flanged LDMOST ceramic package; 6 leads

SOT1239B

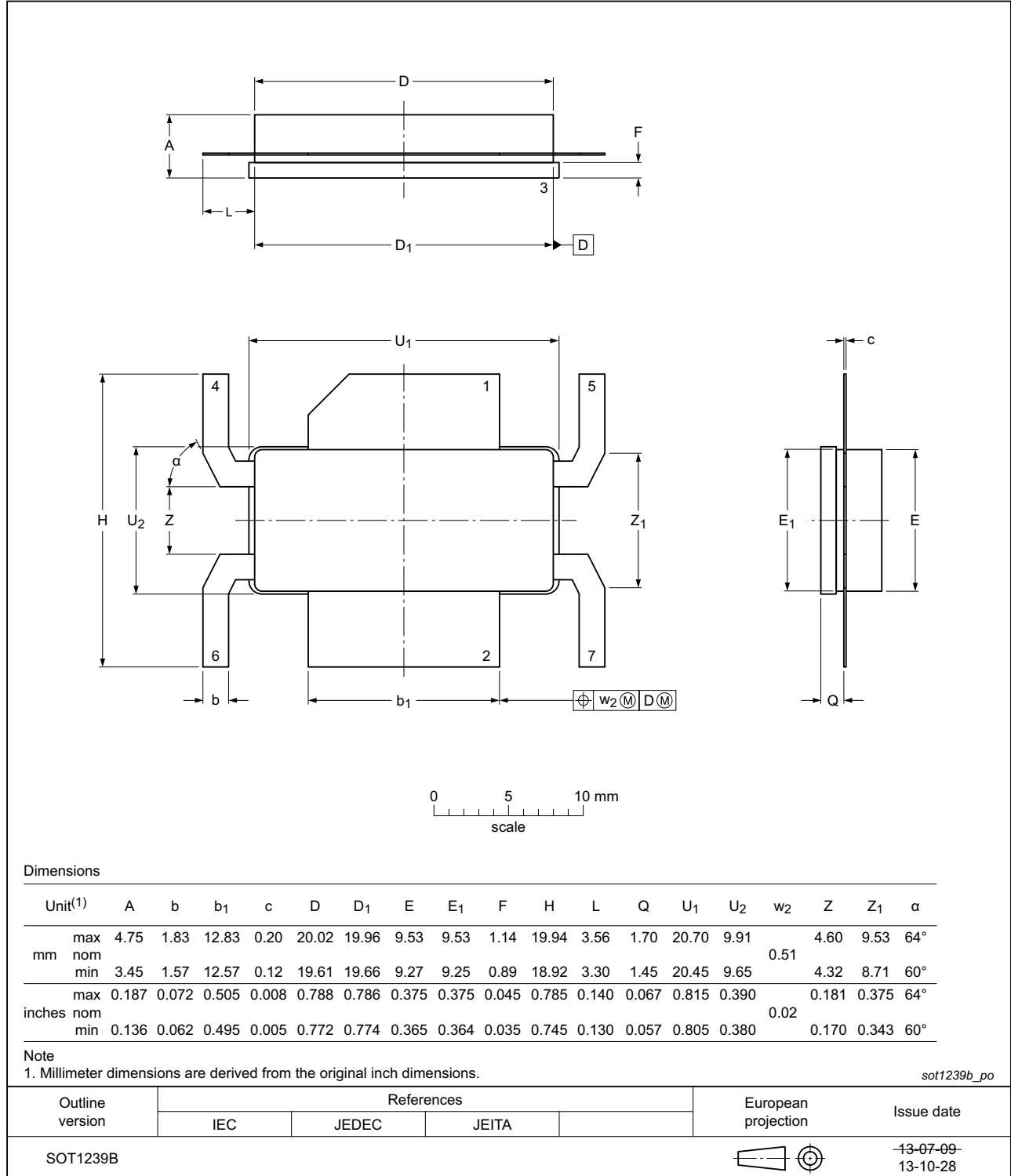


Fig 6. Package outline SOT1239B

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 9. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF8G38LS-75V v.1	20131104	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 4 November 2013

Document identifier: BLF8G38LS-75V